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APPROVAL SHEET

Customer:	
Part Number:	
Part No.:	11414100000.0009
Holder:	OCXO-14
Frequency:	100MHz
Manufacturer:	
Date:	2023-03-22

Prepared	Checked	Approved

(For Customer Use)

Acceptable	Non-Acceptable

Revision History

No.	Revised Date	Change Content	Approved	Remark
1.0	2023-3-22	Initial Release		

1. Scope

This document describes technical guidelines of product 11414100000.0009

2. Electrical Characteristics

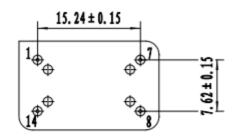
HCMOS OUTPUT OCXO-14								
PARAMETER	SYMBO L	CONDITIONS	MIN	TYPE	MAX	UNIT		
Normal Frequency	Fn	AT1		100		MHz		
Absolute maximum ratings								
Maximum Supply Range	m Supply Vcc –		-0.3		+5.5	V		
Operating Temperature range	TA	_	-30		70	°C		
Storage Temperature range			-55		100	°C		
Power			•					
Operating Supply Voltage	V _{cc}		4.75	5	5.25	V		
Turn-On		Nom Vcc			2.5	W		
Steady state		Ta=25°C			1	W		
Frequency Stat	oility							
Calibration		T _A =25℃			±0.5	ppm		
Freq VS Temperature	Ts	-30°C to 70°C			±200	ppb		
Freq VS Time		Per day			±50	ppb		
(Aging)		1st year			±1.5	ppm		
		10 years			±4	ppm		
Warm up time		time to ±0.5 of F _n			3	minutes		
Output paramet	ters					!		
Output signal		-		HCMOS				
Output load		Output to ground	13.5	15	16.5	pF		

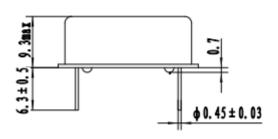
Outrot laval	V _{OH}	High Level	4.5			٧
Output Level	V _{OL}	Low Level			0.5	V
Duty Cycle			45	50	55	%
Rise time/ Fall time					5	ns
		10Hz		-80		dBc/Hz
		100Hz		-110		dBc/Hz
Phase noise		1KHz		-135		dBc/Hz
		10KHz		-145		dBc/Hz

				10KHz		-145		dBc/Hz			
۔ ۔ ا											
	3. Construction 1. Oscillator enclosure seal:										
1.											
_	□Seam se		istance weld	□ cold weld							
2.	crystal enclosu										
	□nitrogen	■vac	uum	□dry air							
1											
1											

4.Dimension:





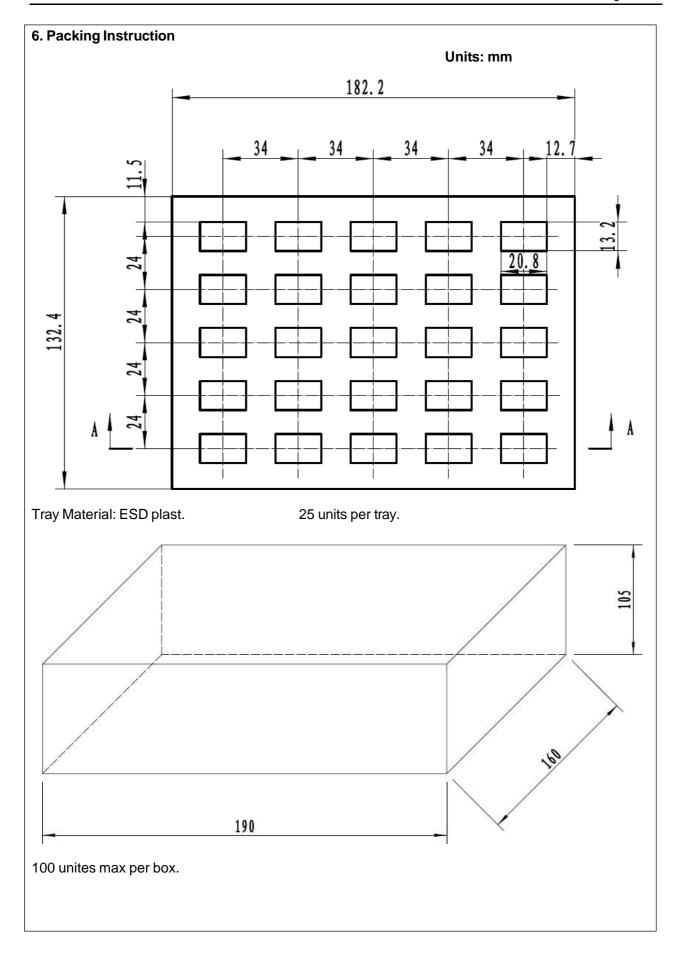


PIN/PAD	FUNCTION:
1	Control Voltage/NC
7	GND
8	Output
14	Power Supply

5. Marking

■ Laser Marking

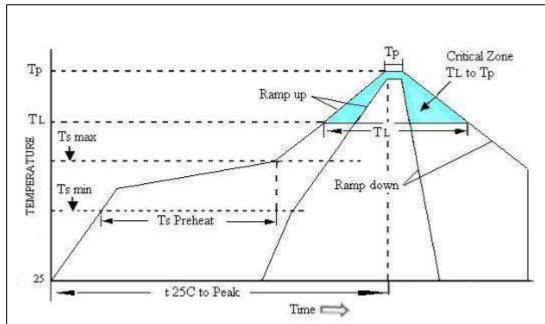
☐ Ink Marking



	Item	Condition	Specifications
. 1	Reflow	3X 240°C Peak	ΔF≤±0.2ppm
• 1	Simulation		220.2pp
	Simulation	20 secs max above 240°C	
. 2	Power Cycl	100 Cycles	ΔF≤±0.2ppm
		-40°C, 30 minutes no power (off) and 30 minutes	
		powered (on)	
		Test product for functionality	
		Continue for another 250 cycles	
		Test product for functionality	
		Intenal visual and mechanical inspection	
. 3	Thermal Shock	Subject samples to temperature extremes of –40 and +125C, 30 minute soaks at the temperature extremes,	ΔF≤±0.2ppm
		10 seconds maximum transition time between	
		extremes. The test duration is 10 Cycles	
		GJB 360A-96 Method 107.	
. 4	Mechanical	IEC 68-2-27 Test Ea	ΔF≤±0.2ppm
• 4	Shock		ΔΕΞΞΟ.ΖΡΡΙΙΙ
. 5	Vibration	IEC 68-2-06 Test Fc	ΔF≤±0.2ppm
7.6	Free drop	Drop from 10cm height on 3cm hard wooden board for 6 times	ΔF≤±0.2ppm
		GB2423.8-1995 (idt IEC 68-2-32:1990) Method Ed。	
. 7	Aging	Bias oscillators at nominal voltage and subject	Per. Spec.
		oscillators to 25C for 1008 hours. Readings are to be	
		taken with oscillator at 25C twice per day. Determine	
		aging (frequency shift post 1008 hours minus initial	
		frequency). Use the results to predict long-term aging.	
. 8	Solderability	Precondition parts by steaming (over boiling water) for 8	A new uniform coating of solder shall cover a minimum
		hours OR age the parts at 150C for 16 hours	of 95% of the surface being

8.All products are RoHs compliant

9. Reflow Profile



High Temperature Infrared /Convection

Note:Temperature shown are applied to body of device

Ts max to T _L (Ramp-up Rate)	3°C/second max		
Preheat			
Temperature Min(Ts Min)	150℃		
Temperature Typical(Ts Typ)	175℃		
Temperature Max.(Ts Max)	200℃		
Time(ts)	60-180 seconds		
Ram-up Rate(T _L to Tp)	3°C/second Max		
Time Maintained Above:			
Temperature(T _L)	217℃		
Time(T _L)	60-150seconds		
Peak Temperature (Tp)	260°C Max for 10 seconds		
Time within 5°C of actual peak(t _p)	20-40 seconds		
Ramp-down Rate	6°C/seconds Max		
Tune 25°C to Peak Temperature(t)	8 minutes Max		
Moisture Sensitivity Level	Level 1		

High Temperature Manual Soldering

Note:Temperature shown are applied to body of device